

AMENDMENTS TO THE CLAIMS

Please amend Claim 129 as follows:

1 - 76. (Cancelled)

77. (Previously Presented) A method for making a thin film semi-conductor comprising the steps of:

providing a semi-conductor substrate having a surface;
forming a first porous layer adjacent said surface having a first porosity;
forming a second porous layer having a second porosity higher than said first porosity;
forming a semi-conductor film on said surface; and
separating said semi-conductor film from said semi-conductor substrate.

78 - 106. (Cancelled)

107. (Previously Presented) A method for making a thin film semi-conductor comprising the steps of:

providing a semi-conductor substrate having a surface;
forming a first porous layer adjacent said surface having a first porosity;

forming a second porous layer within said first porous layer having a second porosity higher than said first porosity;

forming at least one semi-conductor film on said surface; and

separating said semi-conductor film from said semi-conductor substrate.

108-128. (Cancelled)

129. (Currently Amended) A method for making a semiconductor film comprising the steps of:

providing a semi-conductor substrate having a surface;

forming a porous layer adjacent said surface, the porous layer comprises a first porous layer having a first porosity and a second porous layer having a second porosity higher than said first porosity and a third porous layer having a third porosity ~~different from said second porosity equal to the first porosity, wherein said second porous layer is disposed between said first porous layer and said third porous layer;~~

forming at least one semi-conductor film on said surface; and

separating semiconductor film from said semi-conductor substrate.

130 - 134. (Cancelled)

135. (Previously Presented) A method for making a thin film semi-conductor comprising the steps of:

forming a first porous layer having a first porosity on a surface of a substrate;

forming a second porous layer having a second porosity higher than said first porosity;

forming at least one semi-conductor thin film on said surface; and

separating said semi-conductor film from said substrate along a line of relative weakness defined in or adjacent one of said first and second porous layer,

wherein said first porous layer and said second porous layer are formed by anodizing.

136. (Previously Presented) A method for making a thin film semi-conductor comprising the steps of:

forming a first porous layer having a first porosity on a surface of a substrate;

forming a second porous layer within said first porous layer having a second porosity higher than said first porosity;

forming at least one semi-conductor thin film on said surface; and

separating said semiconductor film from said substrate along a line of relative weakness defined in or adjacent one of said first and second porous layers.

137. (Cancelled)

138. (Previously Presented) A thin film semi-conductor formed by:
providing a semi-conductor substrate having a surface;
forming a first porous layer having a first porosity on a surface of said substrate;
forming a second porous layer having a second porosity higher than said first porosity;
forming at least one semi-conductor thin film on said surface; and
separating said semi-conductor film from said substrate along a line of relative weakness defined in or adjacent one of said first and second porous layers to obtain said thin film semi-conductor,
wherein said first porous layer and said second porous layer are formed by anodizing.

139. (Previously Presented) A thin film semi-conductor formed by:
providing a semi-conductor substrate having a surface;
forming a first porous layer having a first porosity on a surface of said substrate;
forming a second porous layer within said first porous layer having a second porosity higher than said first porosity;
forming at least one semi-conductor thin film on said surface; and
separating said semi-conductor film from said substrate along a line of relative weakness defined in or adjacent one of said first and second porous layers to obtain said thin film semi-conductor.

140 - 141. (Cancelled)

142. (Previously Presented) A thin film semi-conductor formed by:
providing a semi-conductor substrate having a surface;
forming a first porous layer adjacent said surface having a first porosity;
forming a second porous layer within said first porous layer having a second porosity
higher than said first porosity;
forming at least one semi-conductor film on said surface; and
separating said semi-conductor film from said semi-conductor substrate along a line of
relative weakness defined in or adjacent one of said first and second porous layers.

143 - 156. (Cancelled)

157. (Previously Presented) A method for making a thin film semi-conductor
comprising the steps of:
providing a semi-conductor substrate having a surface;
forming a first porous layer adjacent said surface having a first porosity;
forming a second porous layer within said first porous layer having a second porosity
higher than said first porosity; and
separating an upper portion of said semi-conductor substrate from said
semi-conductor substrate along a line of relative weakness defined in or adjacent said second
porous layer.

158 - 159. (Cancelled)